

# MOS FIELD EFFECT TRANSISTOR

## NP88N075CUE, NP88N075DUE, NP88N075EUE

### SWITCHING

### N-CHANNEL POWER MOS FET

### INDUSTRIAL USE

#### DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

#### FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance  
 $R_{DS(on)} = 8.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 44 \text{ A)}$
- Low  $C_{iss}$  :  $C_{iss} = 8200 \text{ pF TYP.}$

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DSS}$	75	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GSS}$	$\pm 20$	V
Drain Current (DC) <sup>Note1</sup>	$I_{D(DC)}$	$\pm 88$	A
Drain Current (Pulse) <sup>Note2</sup>	$I_{D(pulse)}$	$\pm 352$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T1}$	288	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_{T2}$	1.8	W
Channel Temperature	$T_{ch}$	175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	$-55 \text{ to } +175$	$^\circ\text{C}$
Single Avalanche Current <sup>Note3</sup>	$I_{AS}$	69 / 88	A
Single Avalanche Energy <sup>Note3</sup>	$E_{AS}$	450 / 14	mJ

**Notes** 1. Calculated constant current according to MAX. allowable channel temperature.

2.  $PW \leq 10 \mu\text{s}$ , Duty cycle  $\leq 1\%$

3. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \rightarrow 0 \text{ V}$

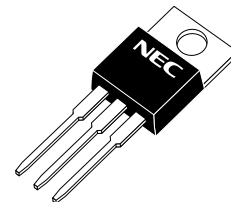
#### THERMAL RESISTANCE

Channel to Case Thermal Resistance	$R_{th(ch-C)}$	0.52	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

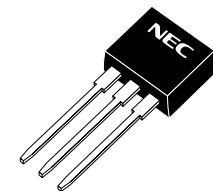
#### ORDERING INFORMATION

PART NUMBER	PACKAGE
NP88N075CUE	TO-220AB
NP88N075DUE	TO-262
NP88N075EUE	TO-263

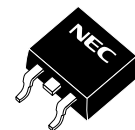
(TO-220AB)



(TO-262)



(TO-263)



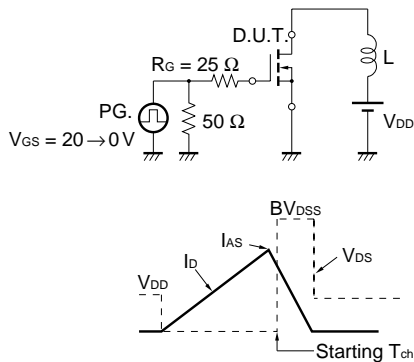
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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

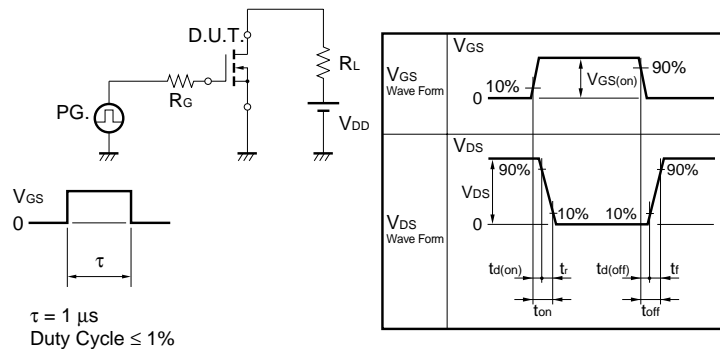
ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V			10	μA
★ Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±100	nA
Gate to Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	3.0	4.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 44 A	30	60		S
Drain to Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 44 A		6.2	8.5	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V		8200	12300	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		800	1200	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		440	800	pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 38 V, I <sub>D</sub> = 44 A		35	77	ns
Rise Time	t <sub>r</sub>	V <sub>GS(on)</sub> = 10 V		28	70	ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 0 Ω		105	210	ns
Fall Time	t <sub>f</sub>			16	40	ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 60 V		150	230	nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V		30		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 88 A		52		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 88 A, V <sub>GS</sub> = 0 V		1.0		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 88 A, V <sub>GS</sub> = 0 V		80		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		240		nC

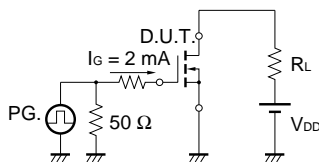
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Figure1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

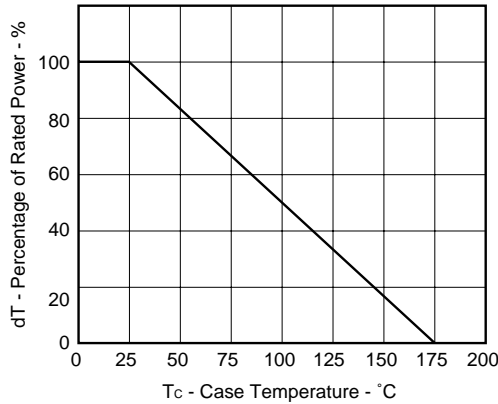


Figure2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

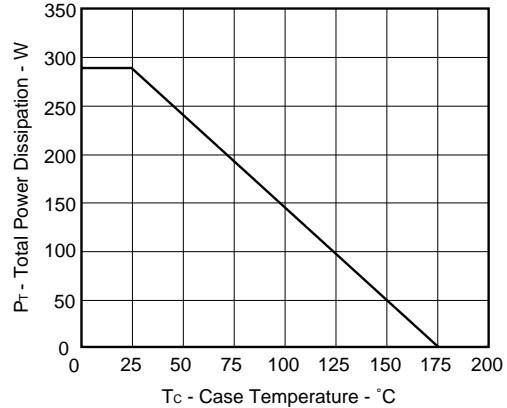


Figure3. FORWARD BIAS SAFE OPERATING AREA

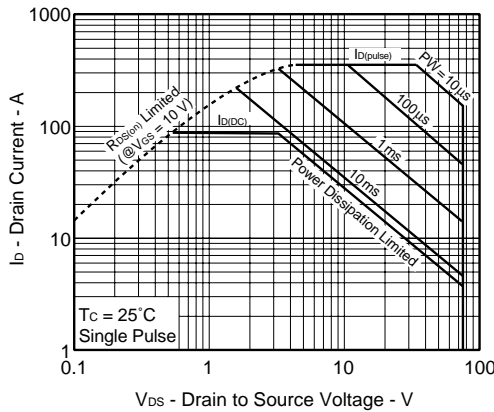


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

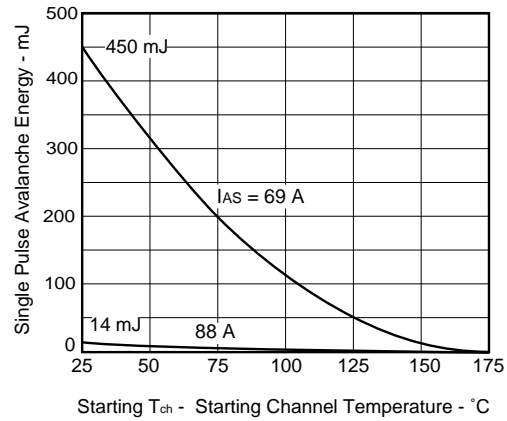


Figure5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

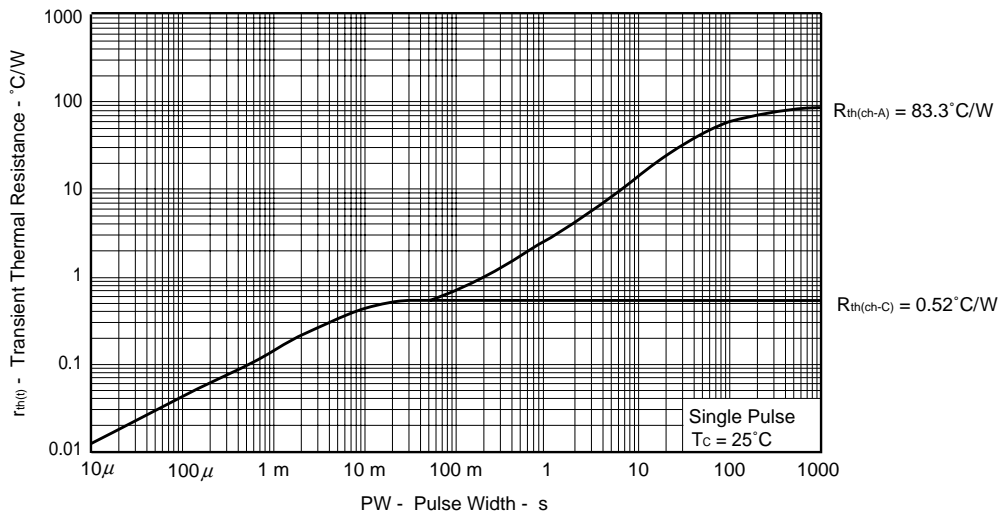


Figure6. FORWARD TRANSFER CHARACTERISTICS

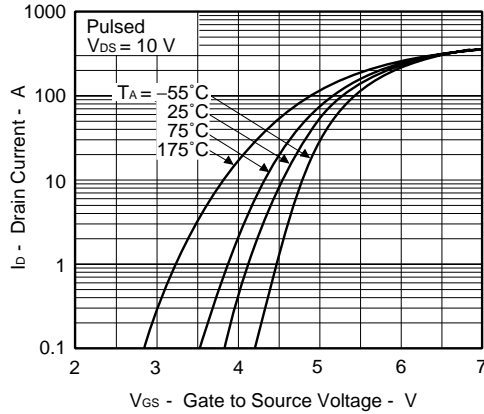


Figure7. DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

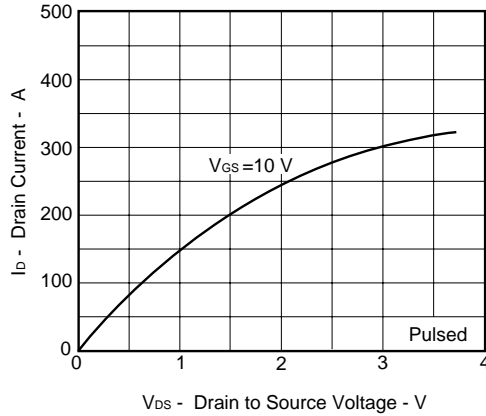


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

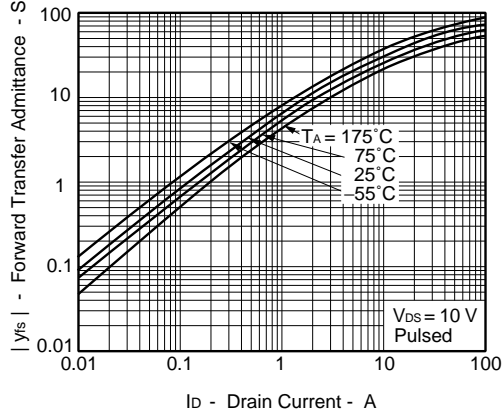


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

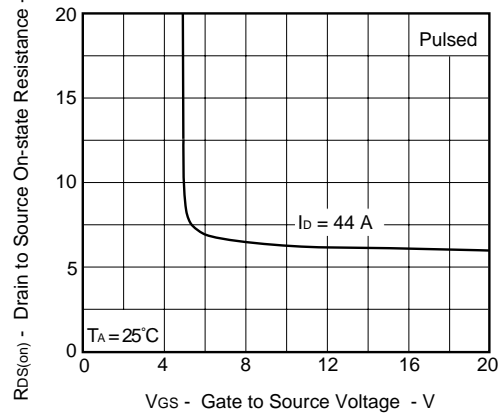


Figure10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

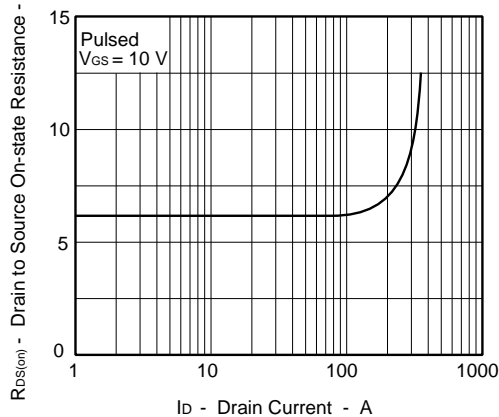


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

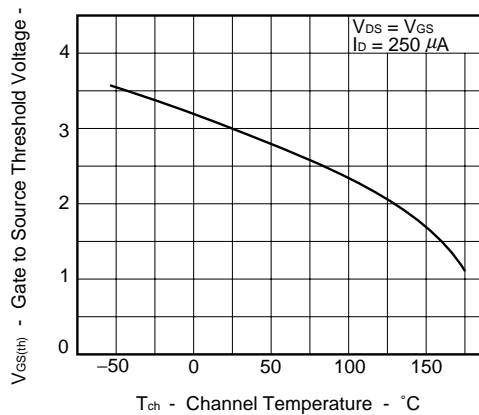


Figure12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

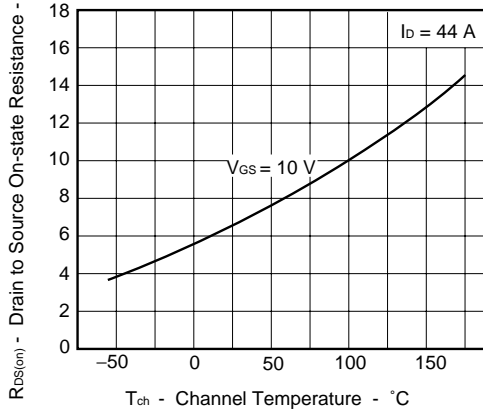


Figure13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

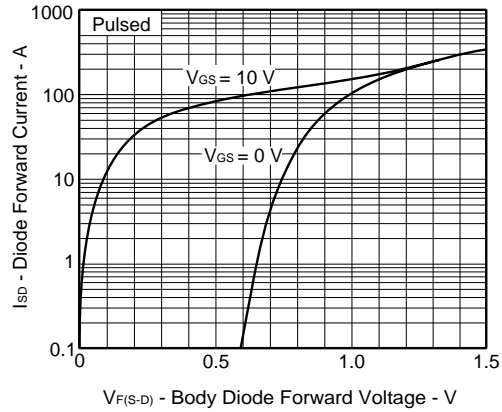


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

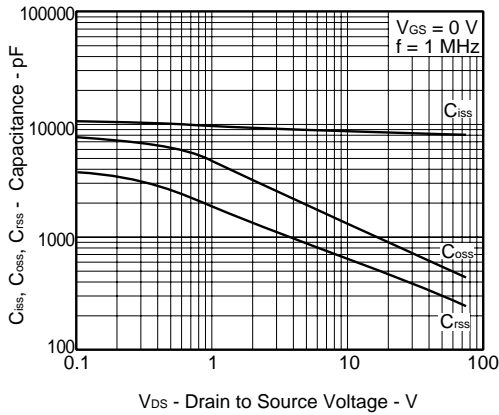


Figure15. SWITCHING CHARACTERISTICS

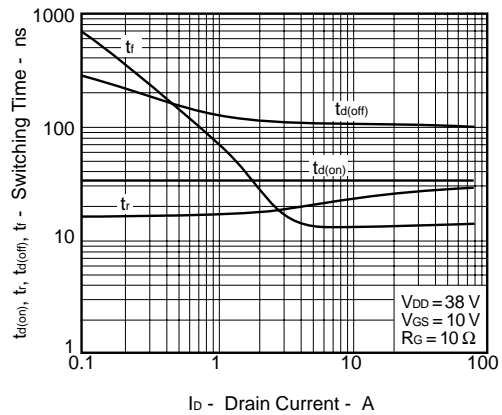


Figure16. REVERSE RECOVERY TIME vs. DRAIN CURRENT

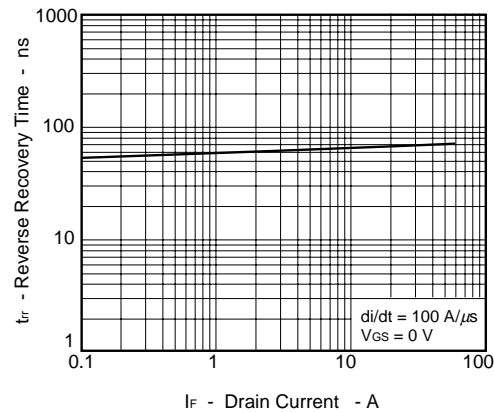
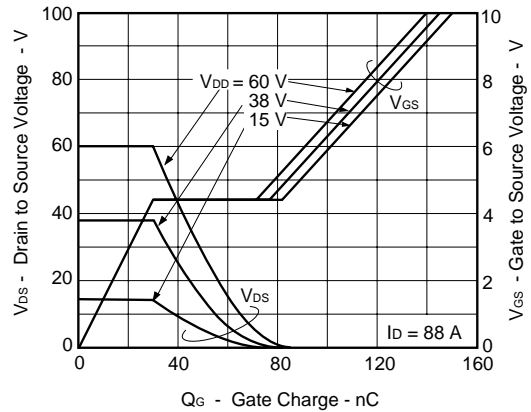
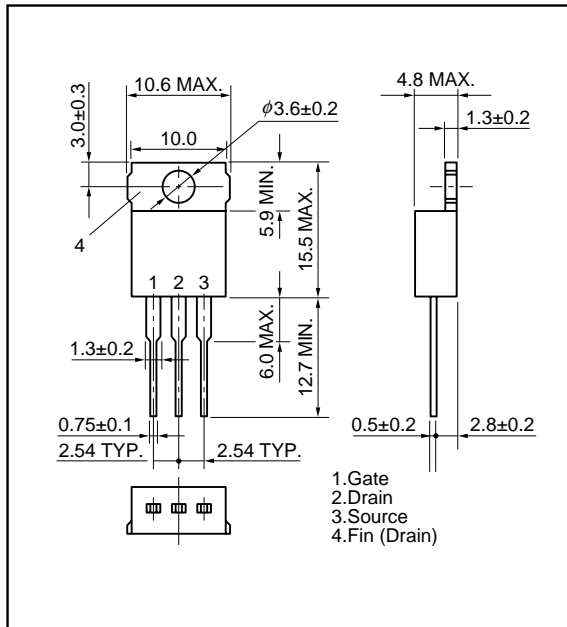


Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

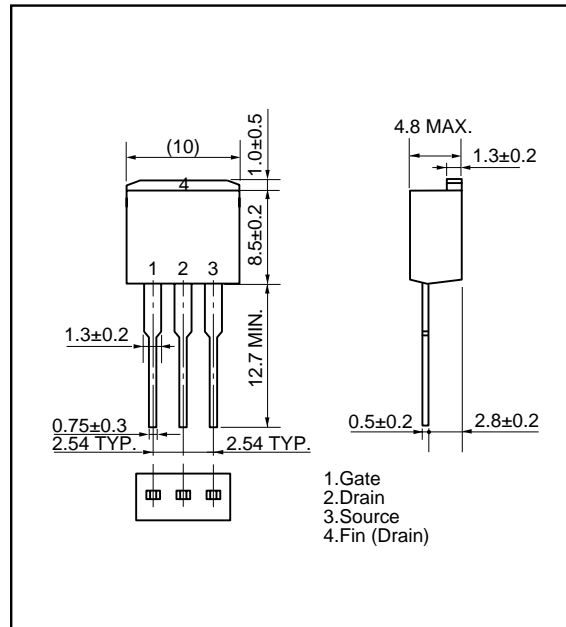


PACKAGE DRAWINGS (Unit: mm)

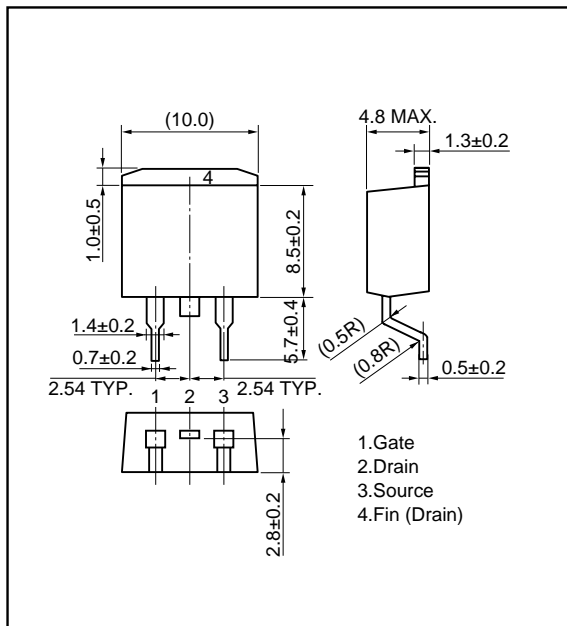
1) TO-220AB (MP-25)



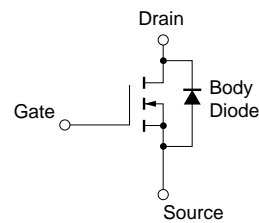
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

[MEMO]

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